

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9	"5762706"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:52
L2	3714	hemt and (electron near9 mobility)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:53
L3	26	hemt and (electron near9 mobility) and "n-InGaP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:53
L4	22	hemt and (electron near9 mobility) and "n-InGaP" and InGaAs	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:54
L5	18	hemt and (electron near9 mobility) and "n-InGaP" and (InGaAs near9 channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:54
L6	3	hemt and (electron near9 mobility) and "n-InGaP" and (InGaAs near9 channel) and (InGaAs near9 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:55
S1	18031	((semiconductor or wafer or substrate) near epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:23
S2	10	((semiconductor or wafer or substrate) near epitaxial) and "FET" and "InGaP" and "n-type" and temperature and mobility and electron and space\$3 and channel and "MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:44

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S3	189	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 07:41
S4	41	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 07:42
S5	25	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:10
S6	33	epitaxial near9 (substrate or semiconductor or wafer) and "HEMT" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:24
S7	14	epitaxial near9 (substrate or semiconductor or wafer) and "HEMT" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and (room near4 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:24
S8	455	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:35
S9	220	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:36
S10	202	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:38

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S11	77	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature and fet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:38
S12	29	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature and fet and pseudomorphic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:55
S14	7	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature and fet and pseudomorphic and channel and (suppl\$4 near layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:58
S15	29	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature and fet and pseudomorphic and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 10:09
S16	6	epitaxial near9 (substrate or wafer or carrier or base) and InGaAs and InGaP and ((n-type or ntype) near9 (inpur\$4 or dop\$4)) and (electron near mobil\$4) and temperature and fet and pseudomorphic and channel and (257/192-194.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 11:40